

Monday June 5th

19h00 - 21h00	Welcome Reception
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Tuesday June 6th

08:00 - 08:30	Opening Ceremony	
08:30 - 10:00	PLENARY SESSION 1 Tu-PS1.1 08:30-09:15: M. Kushimoto , CW operation of UVC lasers Tu-PS1.2 09:15-10:00: J. Kim , 2D materials for UV application Chair: J.P. Salvestrini	
10:00 - 10:30	Coffee break	
10:30 - 12:30	<p style="text-align: center;">A1 – Oxides</p> Tu-A1.1 10:30-10:55: E. Chikoidze , Ultra Wide Band Gap Gallia and Zinc Gallate electronic properties Tu-A1.2 10:55-11:20: T. Onuma , Far UV optical properties of MgO homoepitaxial and Zn doped MgO films prepared by mist chemical vapor deposition method Tu-A1.3 11:20-11:45: G. Fanchini , Defect-Related Optoelectronic and Magnetic Properties of Nanostructured Nickel Oxides as Charge Transport Layers in Organic Photovoltaics Tu-A1.4 11:45-12:00: Z. Liu , Ultrathin and Freestanding Ga ₂ O ₃ Membrane Developed by Thermal Mismatch Engineering for Vertical Electronics Tu-A1.5 12:00-12:15: Y. Zhang , Beta-Gallium Oxide nanowire-based electronic devices and its low frequency noise analysis Chairs: X. Li / A. Osinsky	<p style="text-align: center;">B1 UV Phot/UV Char</p> Tu-B1.1 10:30-10:55: B. Gil , The Optical Properties of Various Polytypes of sp ² -bonded Boron Nitride Tu-B1.2 10:55-11:20: Y. Auad , Cathodoluminescence excitation spectroscopy: revealing the excitation pathways in the nanometer scale Tu-B1.3 11:20-11:45: R. Butte , Polaritonic effects in III-nitride planar waveguides and microring resonators Tu-B1.4 11:45-12:00: B. Szafranski , Time-resolved cathodoluminescence spectroscopy of oxygen related defects in AlN layers Tu-B1.5 12:00-12:15: K. Korona , Time-Resolved UV Photoluminescence of Color Centers in MOCVD-Grown Boron Nitride Tu-B1.6 12:15-12:30: P. Gonzalez-Izquierdo , Kelvin Probe Force Microscopy under variable illumination: a novel technique to unveil charge carrier dynamics in (Al/In/Ga)N Chairs: G. Cassabois / T. Guillet
12:30 - 13:30	Lunch / Poster session	
13:30 - 15:00	<p style="text-align: center;">A2 2D/Nano</p> Tu-A2.1 13:30-13:55: J. K. Kim , Growth of hexagonal boron nitride by MOCVD for DUV applications Tu-A2.2 13:55-14:10: A. Rousseau , Optical Characterization Of Exfoliated Monolayer Boron Nitride By Means Of Hyperspectral Microscopy In The Deep-UV Tu-A2.3 14:10-14:25: V. Ottapilakkal , MOVPE Growth of Thin hexagonal Boron Nitride on Patterned Epigraphene Tu-A2.4 14:25-14:40: J. Rogoza , Fabrication of hexagonal boron nitride membranes on germanium for Raman signal enhancement Chairs: D. Cai / H. Sun	<p style="text-align: center;">B2 UV emitters</p> Tu-B2.1 13:30-13:55: M. Iwaya , Toward enhancement of light output power of AlGaIn-based UV-B laser diodes Tu-B2.2 13:55-14:10: E. Torres-Vasquez , Resonant-cavity UVB LEDs with tunnel-junctions and all-dielectric DBRs Tu-B2.3 14:10-14:25: R. Dupuis , Crack suppression of high Al-mole-fraction AlGaIn layers on patterned GaN substrates for ultraviolet light emitting diodes and laser diodes Tu-B2.4 14:25-14:40: J. Rass , UV micro-LEDs and micro-LED arrays for high efficiency and new applications Tu-B2.5 14:40-14:55: E. Akar , GaN Nanowire Ensembles Ultraviolet Photodetectors based on Photoconductors and Schottky Photodiode Chairs: A. Haglund / M. Dawson
15:00 - 15:30	Coffee break	
15:30 - 17:30	<p style="text-align: center;">A3 AlGaIn/AlN</p> Tu-A3.1 15:30-15:55: S. Hagedorn , Fabrication of high-quality AlN and AlGaIn templates Tu-A3.2 15:55-16:20: K. Uesugi , Homo-epitaxial growth on high temperature annealed AlN template and device applications Tu-A3.3 16:20-16:35: Y. Guo , Improved crystallinity and surface morphology of a-plane AlN grown on r-sapphire by pulsed-flow Mode MOVPE Tu-A3.4 16:35-16:50: C. Margenfeld , Point Defect Engineering for Enhanced Dislocation Annihilation During High-Temperature Annealing of AlN Templates Tu-A3.5 16:50-17:05: P. Vuong , Investigation of p-type doping in BAlN alloys for deep ultraviolet optoelectronics Tu-A3.6 17:05-17:30: S. Zhao , AlGaIn nanowire LEDs / MBE for UV sources Chairs: R. Dupuis / E. Monroy	<p style="text-align: center;">B3 2D/Nano</p> Tu-B3.1 15:30-15:55: D. Cai , 25-inch hexagonal boron nitride for van der Waals heteroepitaxy and p/n type conduction Tu-B3.2 15:55-16:20: H. Sun , Deep ultraviolet micro LEDs Tu-B3.3 16:20-16:45: B. Daudin , AlN nanowire LEDs Tu-B3.4 16:45-17:00: Z. Liu , Principles for 2D Material Assisted Nitrides Epitaxial Growth Tu-B3.5 17:00-17:15: N. Bernhardt , The pursuit of deep-UV defect emitters in 2D hBN Tu-B3.6 17:15-17:30: T. Wei , Graphene-assisted growth of single crystalline GaN on SiO ₂ /Si(100) for monolithic optoelectronic integration and flexible Chairs: J. Kim / M. Tchernycheva
17:30 - 17:45	Coffee break	

Tuesday June 6th

Poster Session

2D/Nano

- Tu-P1** A. Zaiter, Investigating the role of h-BN on the growth of AlN by MBE
Tu-P2 L. Janicki, Dodecagonal III-nitride microrods – a basis for future UV devices
Tu-P3 I. Pugazhendhi, Hybrid CsPbBr₃ quantum dots decorated two dimensional MoO₃ nanosheets photodetectors with enhanced performance
Tu-P4 L. Wang, Threading dislocation defects effecting on the optical gain in GaN terahertz quantum cascade laser
Tu-P5 K. Korona, Kinetics of UV luminescence of LED structures embedded in GaN/AlGaN nanowires
Tu-P6 A. Kaur, Formation of Two Dimensional Electron Gas (2DEG) in Wedge Shaped Nanostructures of GaN: Validation of the Theoretical Model
Tu-P7 V. Ottapilakkal, Growth of Thin BN films on C face Epigraphene using MOVPE
Tu-P8 V. Ottapilakkal, Thermal Stability of Thin hexagonal boron Nitride Grown by MOVPE on Epigraphene
Tu-P9 R. He, Wafer-Scale Exfoliation of AlN Film via hexagonal BN-Assisted van der Waals Epitaxy for Deep-Ultraviolet Light-Emitting Diodes
Tu-P10 F. Tijnt, Hydrogen production and storage using h-BN

AlN/AlGaN

- Tu-P11** L. Peters, Sublimation Behavior of AlN in Nitrogen and Argon at Conditions Used for High-Temperature Annealing
Tu-P12 D. Lee, The effect of thermally treated AlN powder on defect formation of AlN single crystals
Tu-P13 Z. Kushitashvili, UV Stimulated Technology Receiving Nanoscale III- Nitrides
Tu-P14 A. Kaminska, Influence of strain on the excitonic bandgap of AlN epitaxial layers grown on Si and sapphire substrates

Oxides

- Tu-P16** T. Hubacek, Surface morphology of diamond grown on III-nitrides layers
Tu-P17 J. Batysta, Optical properties of diamond layers grown on III-nitrides
Tu-P18 E. Butanovs, The Effect of a Nucleation Layer on Morphology and Grain Size in MOCVD-Grown β -Ga₂O₃ Thin Films on C-Plane Sapphire
Tu-P19 Z. Chi, Zn Doping Effect on Electrical Transport Properties in β -Ga₂O₃
Tu-P20 I. Zhelezova, Vacancy defects in Si doped β -(Al,Ga)₂O₃

UV Phot/UV Emit.

- Tu-P21** S. Arora, Electroluminescence Study of Spatially Indirect Interfacial Excitons in n-ZnO/p-GaN Heterostructures
Tu-P22 J. Yoshinaga, Epitaxial growth of AlGaN-based deep-ultraviolet light-emitting diodes on a 6-inch sputter-annealed AlN template by using MOCVD system for mass production
Tu-P23 R. Ren, Lasing threshold reduction of AlGaN based UV-C laser diodes on strain relaxed lower cladding layer
Tu-P24 R. Hernandez, Flexible nanowire UV LEDs
Tu-P25 F. Dominec, Roughness and doping effects on p-diamond/n-nitride heterointerface diodes

Award Committee: G. Cassabois / J.P. Salvestrini / D. Rogers / M. Tchernycheva / J. Brault / E. Monroy / T. Guillet / T. Wang / A. Kaminska / M. Weyers

17:45
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19:30

Wednesday June 7th

08:30 – 10:00	PLENARY SESSION 2	
	<p>We-PS2.1 08:30-09:15: H. Miyake, Sputtering growth of AlN for high quality template and its application for UV LEDs</p> <p>We-PS2.2 09:15-10:00: M. Strassburg, UV-C LEDs – from development to today's and future applications</p> <p style="text-align: right;">Chairs: B. Gil</p>	
10:00 – 10:30	Coffee break	
10:30 – 12:30	<p style="text-align: center;">A4 UV Phot/UV Char</p> <p>We-A4.1 10:30-10:45: N. Nikitskiy, Anomalous temperature dependence of the emission properties of (Al,Ga)N quantum dots emitting in the UV range</p> <p>We-A4.2 10:45-11:00: A. Perepelic, On the origin of giant persistent photoconductivity in hexagonal boron nitride</p> <p>We-A4.3 11:00-11:15: J. Plo, Isotopic composition-dependent deep level emission in hexagonal boron nitride</p> <p>We-A4.4 11:15-11:30: P. Shen, A high-responsivity solar-blind photodetecting paper with sandwiched ZnO nanoarray/hexagonal boron nitride monolayer aluminum</p> <p>We-A4.5 11:30-11:45: G. Alvarez, High cross-plane thermal conductivity of h-BN at low thickness grown by pulsed laser deposition</p> <p>We-A4.6 11:45-12:00: R. Katayama, Deep UV light generation by nitride-based second harmonic generation wavelength conversion devices</p> <p style="text-align: right;">Chairs: J.P. Salvestrini / R. Butte</p>	<p style="text-align: center;">B4 UV emitters</p> <p>We-B4.1 10:30-10:55: M. Dawson, Optical Wireless Communication with Ultraviolet micro-LEDs</p> <p>We-B4.2 10:55-11:10: T. Wernicke, Analysis of the radiative recombination efficiency, carrier injection efficiency and light extraction efficiency in 265 nm LEDs</p> <p>We-B4.3 11:10-11:25: D. Apaydin, Optically Pumped UVC Photonic Crystal Surface-Emitting Laser</p> <p>We-B4.4 11:25-11:40: Z. Liu, Machine learning design for UVC light-emitting diodes by stacked XGBoost/LightGBM</p> <p>We-B4.5 11:40-11:55: M. O'Donovan, Impact of alloy disorder on carrier transport and recombination in (Al,Ga)N-based UV-C emitters</p> <p>We-B4.6 11:55-12:10: U. Hansen, Maximizing Light Output of DUV LEDs using Miniaturized Mirrors)</p> <p>We-B4.7 12:10-12:25: J. Hopfner, Unravelling carrier transport in far-UV LEDs by temperature dependent electroluminescence measurements</p> <p style="text-align: right;">Chairs: M. Kneissl / M. Iwaya</p>
12:30 – 13:30	Lunch / Poster session	
13:30 – 15:30	<p style="text-align: center;">A5 Oxides</p> <p>We-A5.1 13:30-13:55: X. Li, Ga₂O₃ research from thermal-induced growth, photodetectors, to integrated circuits</p> <p>We-A5.2 13:55-14:20: A. Osinsky, Growth of high purity and doped β-Ga₂O₃ films using MOCVD</p> <p>We-A5.3 14:20-14:35: M. Bickermann, Gallium Oxide Bulk Crystals Prepared by the Czochralski Method, (100) Substrates, and Homoepitaxy Results</p> <p>We-A5.4 14:35-14:50: D. Rogers, Zinc Oxide Based Electronics & Photonics: Existing & Emergent Applications</p> <p>We-A5.5 14:50-15:05: N. Bernhardt, Energies and Orientations of the Fundamental Direct Optical Transitions in β-Ga₂O₃</p> <p>We-A5.6 15:05-15:20: H. Teisseyre, Is SCAM a promising oxide material, or a scam?</p> <p>We-A5.7 15:20-15:35: R-H. Horng, Material Properties of n-type β-Ga₂O₃ heteroepilayers with In-Situ Doping Grown on Sapphire by Metalorganic Chemical Vapor Deposition</p> <p style="text-align: right;">Chairs: D. Rogers / T. Onuma</p>	<p style="text-align: center;">B5 WBG Phys./Applic.</p> <p>We-B5.1 13:30-13:55: K. Sakowski, Numerical simulations of AlGa_N heterostructures with polarization-doping</p> <p>We-B5.2 13:55-14:20: L. Van Deurzen, Excitonic luminescence in homoepitaxial N-polar AlN grown on bulk substrates</p> <p>We-B5.3 14:20-14:45: A. Khan, Progress and Challenges of Transparent AlGa_N-based UVB LEDs</p> <p>We-B5.4 14:45-15:00: N. Declercq, Ultraviolet light used in a historical case study of 1639</p> <p>We-B5.5 15:00-15:15: E. Nogales, Gallium oxide temperature-dependent refractive index and Cr doped β-Ga₂O₃ nanowires as thermometers</p> <p style="text-align: right;">Chairs: R. Kudrawiec / W. Miller</p>
15:30 – 16:00	Coffee break	
16:00 – 17:45	<p style="text-align: center;">A6 WBG Phys./Applic.</p> <p>We-A6.1 16:00-16:25: R. Kudrawiec, Studies of the electric field distribution in III-N heterostructures and the position of the Fermi level at the van der Waals/III-N interface by contactless electroreflectance in UV</p> <p>We-A6.2 16:25-16:50: W. Miller, Growth kinetics of AlN and AlGa_N deposition on AlN(0001): A kinetic Monte Carlo Study</p> <p>We-A6.3 16:50-17:15: J. Ruschel, Degradation effects - Similarities and differences of UV LEDs with different wavelengths</p> <p>We-A6.4 17:15-17:30: S. Schmult, Highly UV-sensitive AlGa_N/Ga_N Heterostructures grown by MBE</p> <p>We-A6.5 17:30-17:45: A. Srivastava, Electrical Characteristics of p-BN/n-AlGa_N Heterostructures</p> <p style="text-align: right;">Chairs: K. Sakowski / A. Khan</p>	<p style="text-align: center;">B6 UV emitters</p> <p>We-B6.1 16:00-16:25: J. Yan, Deep-ultraviolet light-emitting diodes integrated with h-B(Al)</p> <p>We-B6.2 16:25-16:40: Z. Liu, Investigation of novel multi-wavelength and broadband AlGa_N-based UV light emitting diodes employing grading transition layers</p> <p>We-B6.3 16:40-16:55: R. He, Monolithically integrated AlGa_N-based ultraviolet-C photonic chips for solar-blind communications</p> <p>We-B6.4 16:55-17:10: F. Nippert, Carrier dynamics in 230nm-emitting AlGa_N quantum wells</p> <p>We-B6.5 17:10-17:25: T. Guillet, Ridge Ga_N polariton lasers: short lasers for on-chip integration</p> <p>We-B6.6 17:25-17:40: L Valera, M-plane AlGa_N digital alloy for microwire UV-B LEDs</p> <p style="text-align: right;">Chairs: M. Dawson / M. Weyers</p>
19:00 – 23:00	Banquet	

Thursday June 8th

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08:30 – 10:00	<p style="text-align: center;">PLENARY SESSION 3</p> <p>Th-PS3.1 08:30-09:15: A. Allerman, UV Power device Th-PS3.2 09:15-10:00: M. Kneissl, State-of-the-art of UV LEDs</p> <p style="text-align: right; color: #c00000;">Chairs: M. Strassburg</p>				
10:00 – 10:30	<p style="text-align: center;">Coffee break</p>				
10:30 – 12:30	<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th style="background-color: #fce4d6; text-align: center;">A7 2D/Nano</th> <th style="background-color: #e2efda; text-align: center;">B7 UV emitters</th> </tr> </thead> <tbody> <tr> <td style="background-color: #fce4d6; vertical-align: top;"> <p>Th-A7.1 10:30-10:55: S. Sundaram, Layered Boron Nitride for deep UV optoelectronics Th-A7.2 10:55-11:10: E. Vuillermet, Surface nano-structuration of 4H-SiC by controlled high-temperature annealing Th-A7.3 11:10-11:25: S. Novikov, High-temperature molecular beam epitaxy of hexagonal boron nitride and hBN-graphene-hBN lateral heterostructures Th-A7.4 11:25-11:40: N. Gao, Enhancing deep-UV sub-250 nm light emission based on truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets Th-A7.5 11:40-11:55: J. Pernot, Shallow donors and DX states in AlN Nanowires Th-A7.6 11:55-12:10: L. Valera, Wire-based UV-μLED using GaN and AlN microwires as template Th-A7.7 12:10-12:25: Z. Liu, Transferable Ga₂O₃ Membrane Exfoliated from Muscovite Mica Platform for Vertical Electronics</p> <p style="text-align: right; color: #c00000;">Chairs: B. Daudin / K. Uesugi</p> </td> <td style="background-color: #e2efda; vertical-align: top;"> <p>Th-B7.1 10:30-10:55: A. Haglund, Ultraviolet emitting vertical cavity surface emitting lasers Th-B7.2 10:55-11:10: S. Huang, Deep-UV distributed Bragg reflectors with 93% reflectivity for low threshold lasers Th-B7.3 11:10-11:25: G. Cardinali, Single-mode operation of optically pumped UVB VCSELs enabled by circular surface structures Th-B7.4 11:25-11:40: A. Kaminska, Emission properties of GaN/AlN and AlGaN/AlN polar multi-quantum wells – experimental and ab initio study Th-B7.5 11:40-11:55: A. Zaiter, Growth of (Al, Ga)N Quantum Dots on h-BN and Exfoliation Processes towards the Fabrication of Flexible Efficient UV-C LEDs Th-B7.6 11:55-12:10: R. Zhang, AlGa_n multiple quantum wells regrown on N-polar AlN/4H-SiC template fabricated by sputtering and high temperature annealing Th-B7.7 12:10-12:25: N. Maeda, Current-induced p-type activation of Mg-doped and highly Al compositional ($x > 0.8$) AlGa_n observed during initial energization of 220 nm band far-UVC LEDs</p> <p style="text-align: right; color: #c00000;">Chairs: A. Allermann / H. Myake</p> </td> </tr> </tbody> </table>	A7 2D/Nano	B7 UV emitters	<p>Th-A7.1 10:30-10:55: S. Sundaram, Layered Boron Nitride for deep UV optoelectronics Th-A7.2 10:55-11:10: E. Vuillermet, Surface nano-structuration of 4H-SiC by controlled high-temperature annealing Th-A7.3 11:10-11:25: S. Novikov, High-temperature molecular beam epitaxy of hexagonal boron nitride and hBN-graphene-hBN lateral heterostructures Th-A7.4 11:25-11:40: N. Gao, Enhancing deep-UV sub-250 nm light emission based on truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets Th-A7.5 11:40-11:55: J. Pernot, Shallow donors and DX states in AlN Nanowires Th-A7.6 11:55-12:10: L. Valera, Wire-based UV-μLED using GaN and AlN microwires as template Th-A7.7 12:10-12:25: Z. Liu, Transferable Ga₂O₃ Membrane Exfoliated from Muscovite Mica Platform for Vertical Electronics</p> <p style="text-align: right; color: #c00000;">Chairs: B. Daudin / K. Uesugi</p>	<p>Th-B7.1 10:30-10:55: A. Haglund, Ultraviolet emitting vertical cavity surface emitting lasers Th-B7.2 10:55-11:10: S. Huang, Deep-UV distributed Bragg reflectors with 93% reflectivity for low threshold lasers Th-B7.3 11:10-11:25: G. Cardinali, Single-mode operation of optically pumped UVB VCSELs enabled by circular surface structures Th-B7.4 11:25-11:40: A. Kaminska, Emission properties of GaN/AlN and AlGaN/AlN polar multi-quantum wells – experimental and ab initio study Th-B7.5 11:40-11:55: A. Zaiter, Growth of (Al, Ga)N Quantum Dots on h-BN and Exfoliation Processes towards the Fabrication of Flexible Efficient UV-C LEDs Th-B7.6 11:55-12:10: R. Zhang, AlGa_n multiple quantum wells regrown on N-polar AlN/4H-SiC template fabricated by sputtering and high temperature annealing Th-B7.7 12:10-12:25: N. Maeda, Current-induced p-type activation of Mg-doped and highly Al compositional ($x > 0.8$) AlGa_n observed during initial energization of 220 nm band far-UVC LEDs</p> <p style="text-align: right; color: #c00000;">Chairs: A. Allermann / H. Myake</p>
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13:30 – 15:30	<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th style="background-color: #fff2cc; text-align: center;">A8 Oxides</th> <th style="background-color: #e2efda; text-align: center;">B8 AlGa_n/AlN</th> </tr> </thead> <tbody> <tr> <td style="background-color: #fff2cc; vertical-align: top;"> <p>Th-A8.1 13:30-13:55: M. Liao, Diamond-based photodetector Th-A8.2 13:55-14:20: K. Kaneko, GeO₂ as a new power device material Th-A8.3 14:20-14:35: C-Y Huang, β-Ga₂O₃ MOSFETs electrical characteristic study of various etching depths grown on sapphire substrate by MOCVD Th-A8.4 14:35-14:50: B. Mendez, Luminescence of doped Ga₂O₃ nanowires Th-A8.5 14:50-15:05: M. Narayanan, Ga₂O₃: Examining electrical conduction and the role of oxygen vacancies Th-A8.6 15:05-15:20: D. Maestre, Elongated micro- and nanostructures formed by Ni and Mn oxides synthesized by a vapor solid method</p> <p style="text-align: right; color: #c00000;">Chairs: A. Kaminska / E. Chikoidze</p> </td> <td style="background-color: #e2efda; vertical-align: top;"> <p>Th-B8.1 13:30-13:55: R. Dupuis, Improved Yield and Performance of III-N Ultraviolet Avalanche Photodiodes via Ion Implantation Th-B8.2 13:55-14:10: S. Graupeter, UVC LEDs emitting at 265nm grown on strain engineered HTA-AlN/sapphire templates with different offcut angles Th-B8.3 14:10-14:25: L. Peters, Revising the Role of Carbon Impurities in Aluminum Nitride Th-B8.4 14:25-14:40: A. Klump, UV Absorption Spectroscopy for the Quantification of Impurities in PVT-AlN Bulk Crystals Th-B8.5 14:40-14:55: K. Haberland, In-situ growth control during MOVPE of far-UV-C LED structures with optical metrology Th-B8.6 14:55-15:20: X. Wang, High performance AlGa_n-based UVC- and UVB-LEDs on nano patterned sapphire substrate</p> <p style="text-align: right; color: #c00000;">Chairs: M. Bickermann / P. Voss</p> </td> </tr> </tbody> </table>	A8 Oxides	B8 AlGa _n /AlN	<p>Th-A8.1 13:30-13:55: M. Liao, Diamond-based photodetector Th-A8.2 13:55-14:20: K. Kaneko, GeO₂ as a new power device material Th-A8.3 14:20-14:35: C-Y Huang, β-Ga₂O₃ MOSFETs electrical characteristic study of various etching depths grown on sapphire substrate by MOCVD Th-A8.4 14:35-14:50: B. Mendez, Luminescence of doped Ga₂O₃ nanowires Th-A8.5 14:50-15:05: M. Narayanan, Ga₂O₃: Examining electrical conduction and the role of oxygen vacancies Th-A8.6 15:05-15:20: D. Maestre, Elongated micro- and nanostructures formed by Ni and Mn oxides synthesized by a vapor solid method</p> <p style="text-align: right; color: #c00000;">Chairs: A. Kaminska / E. Chikoidze</p>	<p>Th-B8.1 13:30-13:55: R. Dupuis, Improved Yield and Performance of III-N Ultraviolet Avalanche Photodiodes via Ion Implantation Th-B8.2 13:55-14:10: S. Graupeter, UVC LEDs emitting at 265nm grown on strain engineered HTA-AlN/sapphire templates with different offcut angles Th-B8.3 14:10-14:25: L. Peters, Revising the Role of Carbon Impurities in Aluminum Nitride Th-B8.4 14:25-14:40: A. Klump, UV Absorption Spectroscopy for the Quantification of Impurities in PVT-AlN Bulk Crystals Th-B8.5 14:40-14:55: K. Haberland, In-situ growth control during MOVPE of far-UV-C LED structures with optical metrology Th-B8.6 14:55-15:20: X. Wang, High performance AlGa_n-based UVC- and UVB-LEDs on nano patterned sapphire substrate</p> <p style="text-align: right; color: #c00000;">Chairs: M. Bickermann / P. Voss</p>
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16:00 – 16:30	<p style="text-align: center;">AB9 AlGa_n/AlN</p> <p>Th-AB9.1 16:00-16:15: J. Cañas, AlGa_n/AlN quantum dots: Growth optimization for electron-beam pumped deep-UV emitters Th-AB9.2 16:15-16:30: I. Prozhnev, Electrical compensation in Al rich Si-doped 90% AlGa_n determined by positron annihilation and X-ray absorption spectroscopy</p> <p style="text-align: right; color: #c00000;">Chairs: S. Sundaram / J. Brault</p>				
16:30 – 17:00	<p style="text-align: center;">Late News</p> <p>LN.1 16:30-16:45: C.-Y. Huang, Emission-activated interfacial degradation in UVC light-emitting diode on high-quality AlN template LN.2 16:45-17:00: D. Rogers, Development, Qualification and Deployment of 220nm peak response β-(Al)Ga₂O₃ MSM Photodetectors for Observation of the Herzberg Continuum from Space</p> <p style="text-align: right; color: #c00000;">Chairs: R. Dupuis</p>				
17:00 – 18:00	<p style="text-align: center;">Closing</p>				